#### **Testing of Integrated Circuits**

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# Cost of finding failing chip



## Design verification testing

#### (10- 50% of total development costs)



## Production testing



Monitoring of radiation resistance (destructive test)

## Production yield

Yield is calculated from defects per  $mm^2$  ( = exp( - A \* D) ) Typical defect density is of the order of 0.005 - 0.02 defects/mm<sup>2</sup> 100.0 (memories have redundancy) 80.0 Very high production volume technology 61% 0.005 60.0 Yield (%) 40.0 37% 36% 0.02 Low production volume technology 20.0 14% 0.0\_L\_\_\_\_ 100.0 150.0 50.0 200.0 Area (mm<sup>2</sup>)

Price of 100 mm<sup>2</sup> chip compared to 50 mm<sup>2</sup> chip:  $100 \text{ mm}^2/50 \text{ mm}^2 \times 0.61/0.37 = 3.4 \text{ (D=0.01)}$  $100 \text{ mm}^2/50 \text{ mm}^2 \times 0.36/0.14 = 5.3 \text{ (D=0.02)}$ 

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## Typical IC faults



# Reliability of integrated circuits



#### Burn-in testing : Heating up chips to 125 deg. accelerates 1000 hours period to approx. 24 hours.

Static: power supply connected. Dynamic: Power + stimulation patterns. Functional test: Power + stimulation patterns + test.

Temperature cycling: Continuous temperature cycling of chips to provoke temperature gradient induced faults. (Non matching thermal expansion coefficients). Electrical stress: Operation at elevated supply voltage

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## What to test



N=32; test time = 40 seconds. N=64; test time = 6.000 years

Knowledge about topology of circuit must be used to reduce number of test vectors so they can be generated by tester (tester memory: 10K - 10M).

Analog and digital stimuli must be generated from a tightly synchronised system.

## Basic testing terms

CONTROLABILITY: The ease of controlling the state of a node in the circuit.

OBSERVABILITY: The ease of observing the state of a node in the circuit

Example: 4 bit counter with clear

Control of q3:

Set low: perform clear = 1 vector



Set high : perform clear + count to 1000B = 9 vectors

### Testing a node in a circuit

- A: Apply sequence of test vectors to circuit which sets node to demanded state.
- B: Apply sequence of test vectors to circuit which enables state of node to be observed.
- C: The observing test vector sequence must not change state of node.

#### Fault models



#### Problematic faults at transistor level



## Gate level (stuck at 0/1model)



- The gate level stuck at 0/1 is the dominantly used fault model for VLSI circuits, because of its simplicity.
- Fault coverage calculated by fault simulation are always calculated using the stuck at 0/1 model. Other more complicated fault models are to compute intensive for VLSI designs.

Fault coverage = Number of faults detected by test pattern Total number of possible stuck at faults in circuit

# Testability



Number of test vectors (test routines)

- A: Design made with testability in mind. ( ~1 test vector per gate )
- B: Design made without testability in mind but good fault coverage obtained by large effort in making test vectors.
- C: Design very difficult to test even using large effort in test vector generation.

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## Generation of test patterns

- Test vectors made by test engineer based on functional description and schematics. Proprietary test vector languages used to drive tester. (over the wall)
- Test vectors made by design engineer on CAE system. Subset of test patterns may be taken from design verification simulations.
- Generated by Automatic Test Pattern Generators (ATPG). Requires internal scan path
- Pseudo random generated test patterns.
- Fault simulation calculates fault coverage.

Fault coverage found by fault simulations



Requires long simulation times !.

Toggle test ( counts how many times each node has changed) can be used to get a first impression of fault coverage.

## Test development with increased complexity



#### IC testers

High speed high pin count VLSI testers are very expensive and complicated machines. (500 k\$ - 10 M\$ ).

Vector speed: 100 - 1000MHz, Vector depth: 32k - 1G Time resolution: 100ps - 10ps Pin count: 100 - 1024





+ Measurements of DC characteristics

No standard Mixed signal tester exists (mixed signal tests are always special)

Testers must be faster than current IC technology !.

#### Scan Path testing



## Scan path testing

Improving controllability/observability by enabling all storage nodes to be controlled/observed via serial scan path.



Test principle:

- 1: Enable scan mode and scan in control data.
- 2: Disable scan mode and clock chip one cycle.
- 3: Enable scan mode and scan out observing data.

Generation of test vectors: With the high controllability/observability the test vectors can be generated automatically with a ATPG program.

## JTAG standard

IEEE 1149 standard.

Boundary scan to test interconnect between chips.

Internal scan to test chip.

Control and status of built in self test.

Chip ID

Many commercial chips with JTAG standard implemented:

Processors, FPGA, etc.



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Boundary scan enables test of digital board connections. (automatic test generation from netlist of board)
JTAG ID enables verification of correct component type.
Enables access to internal test features in components.
Testing can be also be performed in-situ.

Small and "cheap" test system required.

Many commercial IC's now have JTAG (Processors, FPGA's, etc.)





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# Built In Self Test (BIST)

#### Different schemes of built in (self) test

Include test pattern generator and response check on chip



Make self checking during operation by duplicating all functions



Generate local check sums and check with transformation of previous check sum



Hardware overhead !!

## Trends in IC design

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#### SIA CMOS Roadmap (from 1997, old)

	1997	1999	2001	2003	2006	2009	2012
<b>Technology</b>							
Technology	.25 µm	.18 µm	.15 µm	.13 µm	.10 µm	70 nm	50 nm
Gate Delay Metric CV/I (7)	16-17 ps	12-13 ps	10-12 ps	9-10 ps	7 ps	4-5 ps	3-4 ps
<b>Overall Characteristics</b>							
Logic transistor density	3.7 M/cm <sup>2</sup>	6.2 M/cm <sup>2</sup>	10 M/cm <sup>2</sup>	18 M/cm <sup>2</sup>	39 M/cm <sup>2</sup>	84 M/cm <sup>2</sup>	180 M/cm <sup>2</sup>
DRAM IC size	$170 \text{ mm}^2$	10 240 mm <sup>2</sup>	$10$ $270 \text{ mm}^2$	$40$ $340 \text{ mm}^2$	$100$ $480 \text{ mm}^2$	$670 \text{ mm}^2$	2500
MDU shin size	$300 \text{ mm}^2$	$240 \text{ mm}^2$	270 mm <sup>2</sup>	$430 \text{ mm}^2$	$520 \text{ mm}^2$	$670 \text{ mm}^2$	$750 \text{ mm}^2$
MPU pin count	800 mm	1000	1200	1500	2000	2600	3600
MPU clock frequency	750 MHz	1.2 GHz	1.4 GHz	1.6 GHz	2.0 GHz	2.5 GHz	3 GHz
ASIC clock frequency	300 MHz	500 MHz	600 MHz	700 MHz	900 MHz	1.2GHz	1.5GHz
Power supply voltage	1.8-2.5V	1.5-1.8V	1.2-1.5V	1.2-1.5V	.9-1.2V	.69V	.56V
MPU high power	70 W	90 W	110 W	130 W	160 W	170 W	175 W
MPU low power	1.2W	1.4W	1.7W	2W	2.4W	2.8W	3.3W

**Solutions Exist** 

**Solutions Being Pursued** 

**No Known Solution** 

### Gate and wire delay

- Gate delay decreases
- Wire delay increases
- Copper wires required to take advantage of decreased gate delay
- Place and route critical





## Technology

- Developing new technologies are increasingly expensive
  - Significant changes in fabrication needed for deep submicro technologies:
    - Deep UV lithography with reflective optics or
    - E-beam or
    - X-ray
- Large companies forced to make strategic alliances to finance development of new technologies
  - IBM, Infinion, UMC
  - ST, Phillips, Motorola
  - Others

- CMOS technology changes:
  - Ever decreasing device sizes (higher integration and faster)
    - When will it all end ? 50nm ?
  - Decreasing power supply voltage
  - Copper interconnect
  - Low dielectric constant insulation materials to decrease interconnect capacitance (but hard to exchange SIO<sub>2</sub>)
  - Silicon On Insulator (SOI)
  - Vertical and/or 3D transistors
- Which technology(ies) will take over after CMOS ?
  - Molecular devices ?
  - Quantum devices ?
  - Carbon nano tube devices ?
  - Optical devices ?
  - Single electron transistors ?





Nanotube transistor

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## Production facilities

- About 10 fabs open per year
- Fab Cost ~2 B\$
  - Affordable only for DRAM and very high volume companies
  - Fab-less companies (e.g. Xilinx)
- Technology lifetime 4-5 years
- Completely new fab. needed for next generation technology
- The microelectronics industry is known to have its up and downs (~5 year period) but still continuously increase in value. This makes it hard to plan investments in fabrication facilities

# Design

- Most designs will be based on synthesis except memory, analog and special devices.
- Analog design will become increasingly difficult because of decreased power supply voltage and change of transistor characteristics. (the world is going digital but is at its origin analog)
- Place and route will become (is) the critical tool.
- Crosstalk between digital signals must be taken into account
- High performance tools will be needed for design and verification
- High performance tools will stay expensive and will probably become even more expensive.
- Design and prototyping costs will increase
- New architectures to take advantage of increasing number of transistors (e.g. Vector processing, VLIW)